

# SANYO SEMICONDUCTOR

2SD995

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NPN Triple Diffused Mesa Type Silicon Transistor  
For H-Deflection Output with High Voltage (With Damper Diode)

### Absolute Maximum Ratings at Ta=25°C

Collector to Base Voltage	V <sub>CB0</sub>	2500	V
Collector to Emitter Voltage	V <sub>CE0</sub>	900	V
Emitter to Base Voltage	V <sub>EB0</sub>	6	V
Collector Current	I <sub>C</sub>	3	A
Collector Current (peak)	i <sub>cp</sub>	7	A
Collector Dissipation	P <sub>C</sub>	3	W
	P <sub>C</sub> Tc=25°C	50	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-40~+150	°C

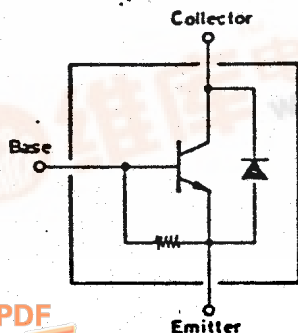
### Electrical Characteristics at Ta=25°C

		min	typ	max	unit
Collector Cut off Current	I <sub>CES</sub> V <sub>CB</sub> =2500V, V <sub>EB</sub> =0			1.0	mA
Emitter Cut off Current	I <sub>EBO</sub> V <sub>BE</sub> =4V, I <sub>C</sub> =0	40		130	mA
Emitter to Base Voltage	V <sub>EB0</sub> I <sub>E</sub> =250mA, I <sub>C</sub> =0	6.0			V
Emitter to Collector Voltage	V <sub>ECO</sub> I <sub>E</sub> =2A, I <sub>B</sub> =0			2.0	V
DC Current Gain	h <sub>FE</sub> V <sub>CE</sub> =10V, I <sub>C</sub> =1.5A	3*		15*	
C-E Saturation Voltage	V <sub>CE(sat)</sub> I <sub>C</sub> =1.5A, I <sub>B</sub> =0.5A			5	V
B-E Saturation Voltage	V <sub>BE(sat)</sub> I <sub>C</sub> =1.5A, I <sub>B</sub> =0.5A			1.3	V
C-E Sustain Voltage	V <sub>CE(sus)</sub> I <sub>C</sub> =100mA, I <sub>B</sub> =0, L=35mH	900			V
Fall Time	t <sub>f</sub> I <sub>C</sub> =1.5A, I <sub>B</sub> =0.6A, t=10 90%			1.0	µs

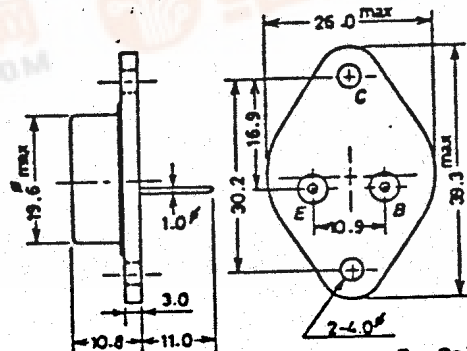
\* 2SD995 are classified according to 1.5A h<sub>FE</sub> as follows.

3 K 9 5 M 15

### Equivalent Circuit



### Case Outline (UNIT:mm)



EIAJ: TC-3, TB-3  
JEDEC: TO-3

C: Collector  
E: Emitter  
B: Base

